

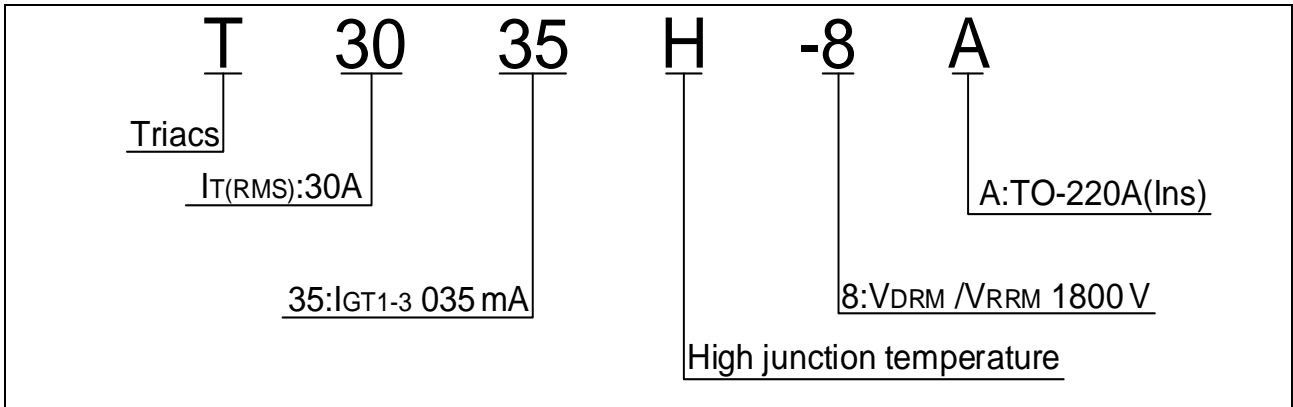
Average gate power dissipation ($T_j=150$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	1	kV

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3k$	- -	MIN.	0.15	V

I_L $I_G=1.2I_{GT}$

ORDERING INFORMATION



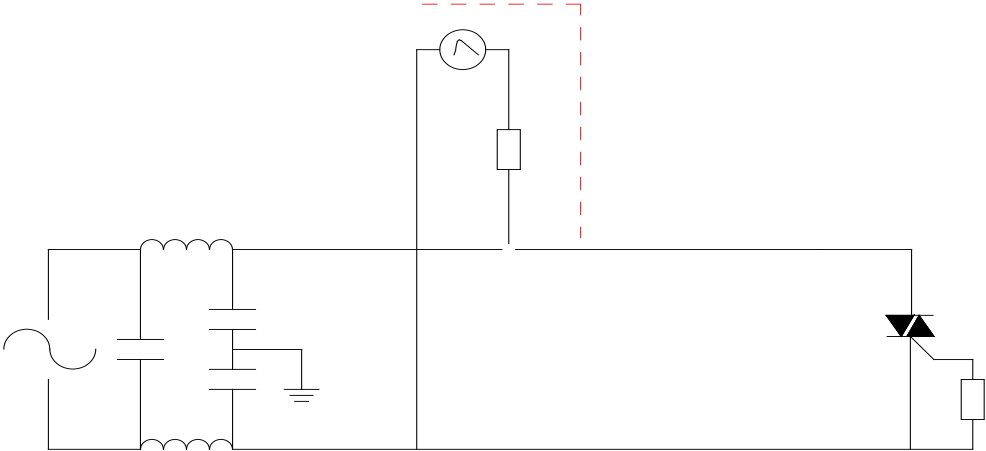
MARKING

FIG.1: Maximum power dissipation versus RMS on-state current



FIG.2: RMS on-state current versus case temperature

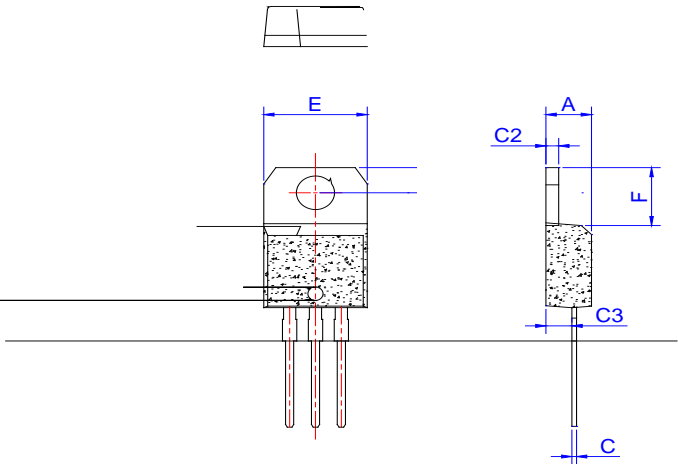
FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	
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PACKAGE MECHANICAL DATA



T3035H-8A

JieJie MoL04 Tc 0 1 TfC2_5.96 0 w 1.394